AMENDMENTS TO THE SPECIFICATION:

Please amend the following paragraph beginning at page 43, line 5 and ending at page 43, line 24 as follows:

FIG. **5A** shows the diffraction phenomenon caused in assuming the oblique incident exposure. Specifically, the light source **140** is disposed in a position away from the normal line (indicated with a long dashed short dashed line in the drawing) extending through the center of a lens **152** by a distance **S**. In this case, the incident angle (the oblique incident angle) φ of the light **141** from the light source **140** against the mask **150** is represented as $\sin\varphi = S \times NA$. Herein, the distance **S** used for defining the oblique incident angle φ is designated as an oblique incident position. The coordinate of the light source **140** is represented by using a value standardized by the numerical aperture **NA**. Also, the diffraction angle θn of nth-order diffraction light (wherein n is an integer) of the light **141** having passed through the pitch patterns **151** arranged at the pitch **P** is represented as $\sin\theta n = n \times \lambda/P$. Also, 0th-order diffraction light **142** of the light ~~140~~ **141** having entered the mask **150** at the oblique incident angle φ reaches a position expressed as a coordinate $r0 = -\sin\varphi = -S \times NA$ on the lens **152** (a coordinate on a one-dimensional coordinate system having the lens center as the origin; which applies to coordinates mentioned below). Furthermore, first-order diffraction light (+first-order diffraction light) **143** of the light ~~140~~ **141** reaches a position expressed as a coordinate $r1 = r0 + \sin\theta 1 = r0 + \lambda/P$. In general, a position on the lens **152** where nth-order diffraction light reaches is expressed as a coordinate $rn = r0 + \sin\theta n = r0 + n \times \lambda/P$, whereas when the absolute value of **rn** exceeds **NA**, the nth-order diffraction light is not diffraction light passing through the lens **152**, and hence is not focused on a wafer.

Please amend the following paragraph beginning at page 51, line 23 and ending at page 52, line 7 as follows:

On the basis of the description given so far, the present inventor has found that in the case where a pattern including a phase shifter as the mask enhancer **110** is used as the main pattern **101** of the photomask according to this embodiment shown in FIG. **1A**, the DOF characteristic in transferring the main pattern **101** through the exposure can be largely improved by arranging, as the auxiliary patterns **102**, patterns that are not transferred through the exposure but generate diffraction lights (namely, diffraction light generation patterns) in predetermined positions. In this case, the predetermined positions are positions away from the center of the phase shifter **101B** of the main pattern **101** (namely, the phase shifter ~~**111B**~~ **112** of the mask enhancer **110**) respectively by a distance $\lambda/(2 \times \sin\varphi)$ and a distance $\lambda/(2 \times \sin\varphi) + n \times \lambda/(\sin\varphi + NA)$ (wherein n is a positive integer).